BC847BFN3

NPN GENERAL PURPOSE TRANSISTORS

VOLTAGE 45 Volts **CURRENT** 250 mWatts

FEATURES

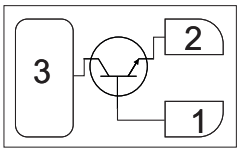
- General purpose amplifier applications
- NPN epitaxial silicon, planar design
- Collector current IC = 100mA
- In compliance with EU RoHS 2002/95/EC directives

MECHANICAL DATA

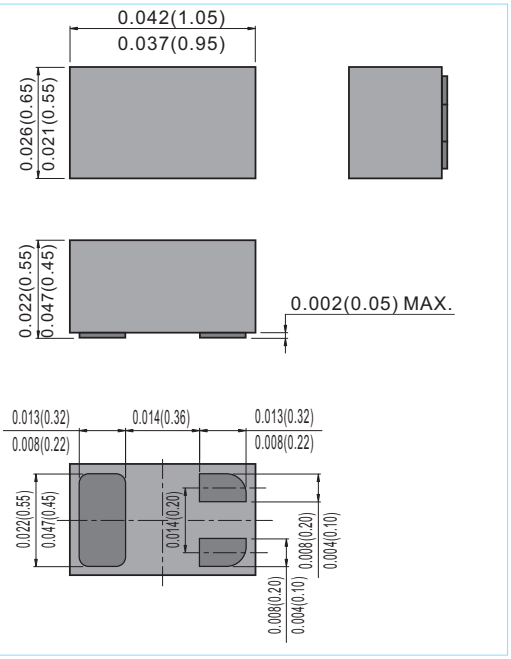
Case: DFN 3L, Plastic

Terminals: Solderable per MIL-STD-750, Method 2026

Marking: AE



DFN 3L Unit : inch(mm)



ABSOLUTE RATINGS

Parameter	Symbol	Value	Units
Collector - Emitter Voltage	V_{CEO}	45	V
Collector - Base Voltage	V_{CBO}	50	V
Emitter - Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous	I_C	100	mA

THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Units
Max Power Dissipation (Note 1)	P_{TOT}	250	mW
Thermal Resistance , Junction to Ambient	$R_{\theta JA}$	500	^{O}C/W
Junction Temperature	T_J	-55 to +150	^{O}C
Storage Temperature	T_{STG}	-55 to +150	^{O}C

Note 1: Transistor mounted on FR-4 board 70 x 60 x 1mm.

PAN JIT RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN,FUNCTIONS AND RELIABILITY WITHOUT NOTICE

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ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise noted)

PARAMETER	Symbol	Test Condition	MIN.	TYP.	MAX.	Unit
OFF CHARACTERISTICS						
Collector - Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=10mA	45	-	-	V
Collector - Emitter Breakdown Voltage	$V_{(BR)CES}$	I_C=10uA, V_{EB}=0	50	-	-	V
Collector - Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=10uA	50	-	-	V
Emitter - Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=10uA	6.0	-	-	V
Collector Cutoff Current	I_{CBO}	V_{CB}=30V, V_{CB}=30V, T_A=150°C	-	-	15 5.0	nA uA
ON CHARACTERISTICS						
DC Current Gain	h_{FE}	I_C=2.0mA, V_{CE}=5V	200	-	450	-
Collector - Emitter Saturation Voltage	$V_{CE(SAT)}$	I_C=10mA, I_B=0.5mA I_C=100mA, I_B=5.0mA	-	- -	0.25 0.6	V
Base - Emitter Saturation Voltage	$V_{BE(SAT)}$	I_C=10mA, I_B=0.5mA I_C=100mA, I_B=5.0mA	0.6 0.8	- -	0.9 1.0	V
Base - Emitter Voltage	$V_{BE(ON)}$	I_C=2mA, V_{CE}=5.0V I_C=10mA, V_{CE}=5.0V	580 -	660 -	700 770	mV
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain-Bandwidth Product	f_T	I_C=10mA,V_{CE}=5.0Vdc,f=100MH_Z	100	-	-	MH_Z
Output Capacitance	C_{obo}	V_{CB}=10V,f=1.0MH_Z	-	-	4.5	pF
Noise Figure	NF	I_C=0.2mA,V_{CE}=5.0Vdc, R_S=2.0kΩ,f=1.0kH_Z , BW=200H_Z	-	-	10	dB

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ELECTRICAL CHARACTERISTICS CURVE

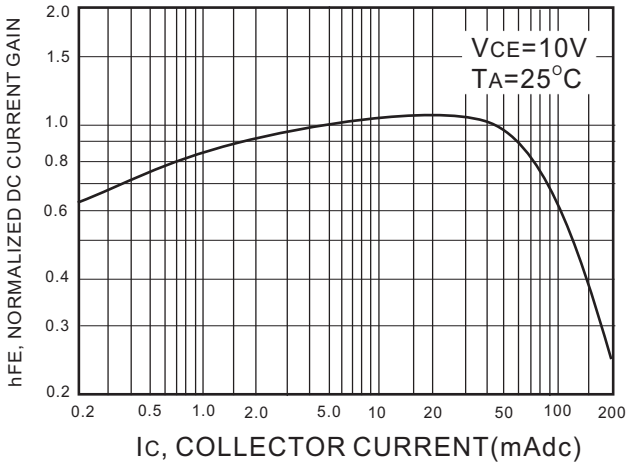

Figure 1. Normalized DC Current Gain

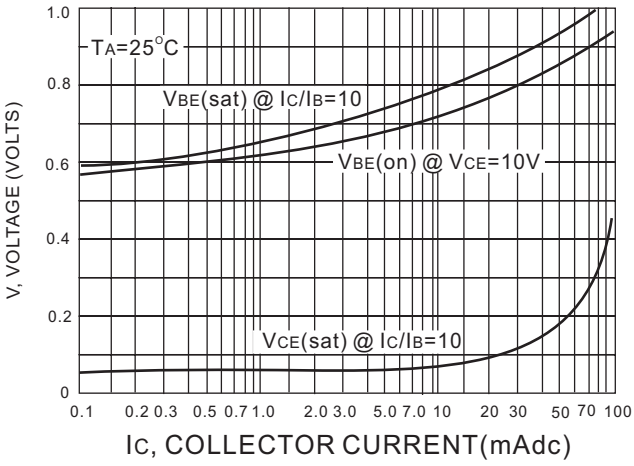

Figure 2. "Saturation" and " On " Voltages

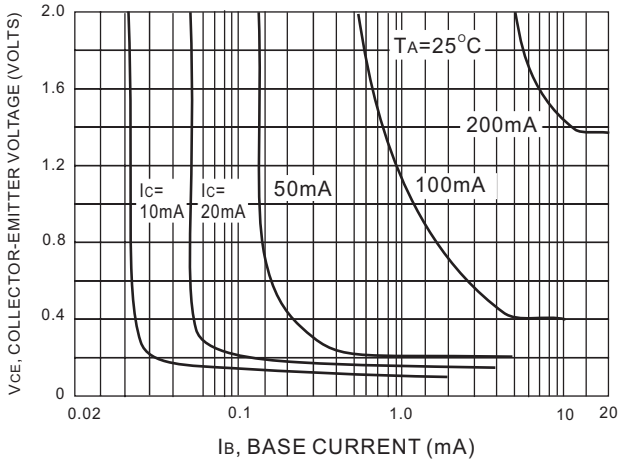

Figure 3. Collector Saturation Region

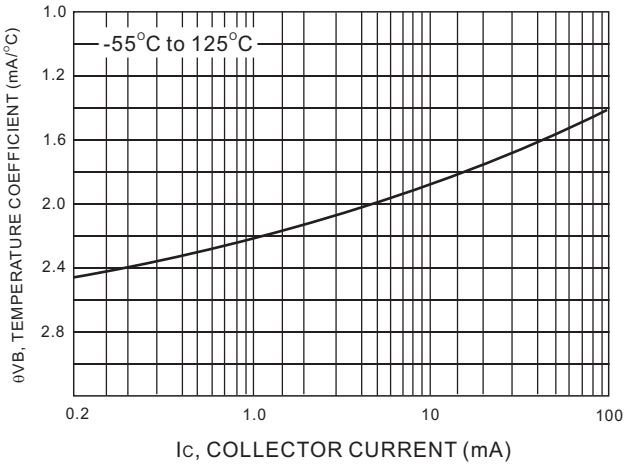

Figure 4. Base-Emitter Temperature Coefficient

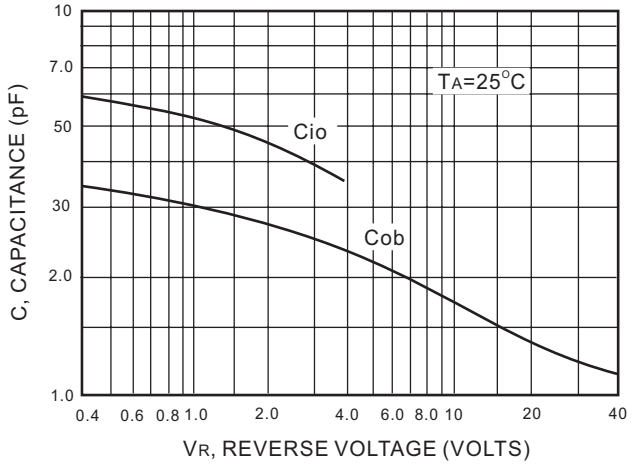

Figure 5. Capacitance

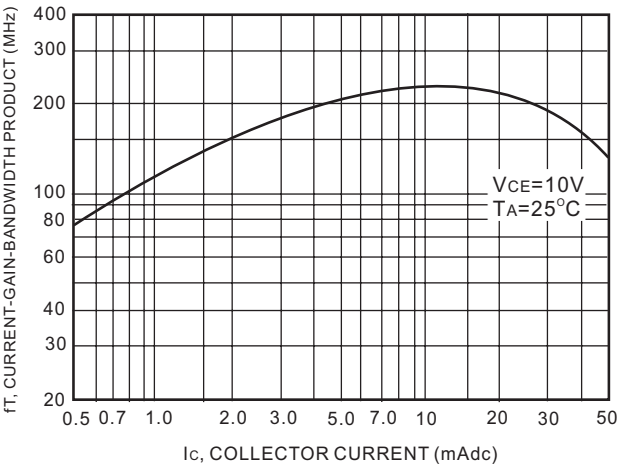

Figure 6. Current-Gain-Bandwidth Product

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ELECTRICAL CHARACTERISTICS CURVE

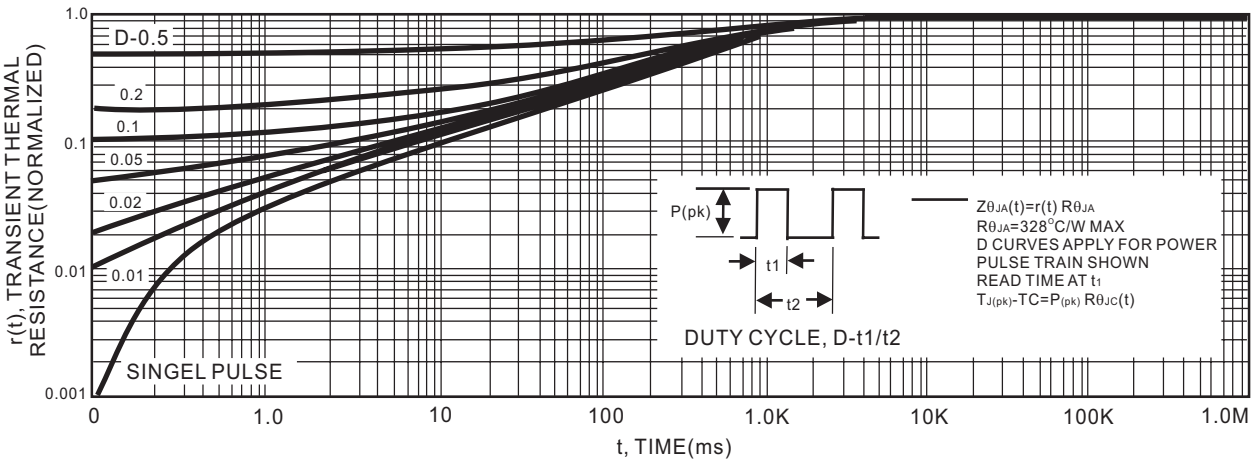

Figure 7. Thermal Response

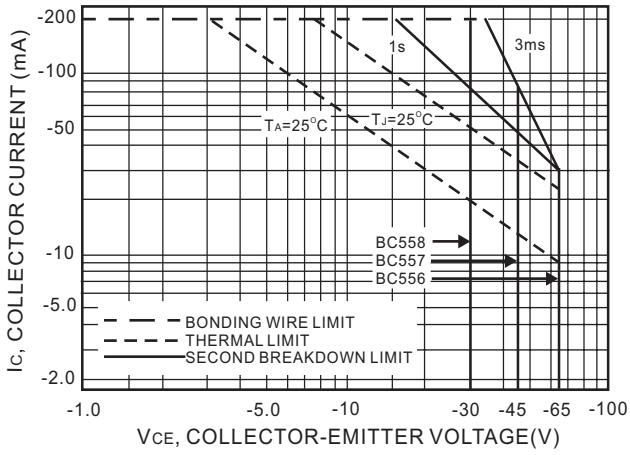

Figure 8. Active Region Safe Operating Area

The safe operating area curves indicate Ic-Vce limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.
The data of Figure 26 is based upon Tj(pk)=150°C; Tc or Ta is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% prodided Tj(pk) < 150°C. Tj(pk) may be calculated from the data in Figure 25. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by the secondary break-down.

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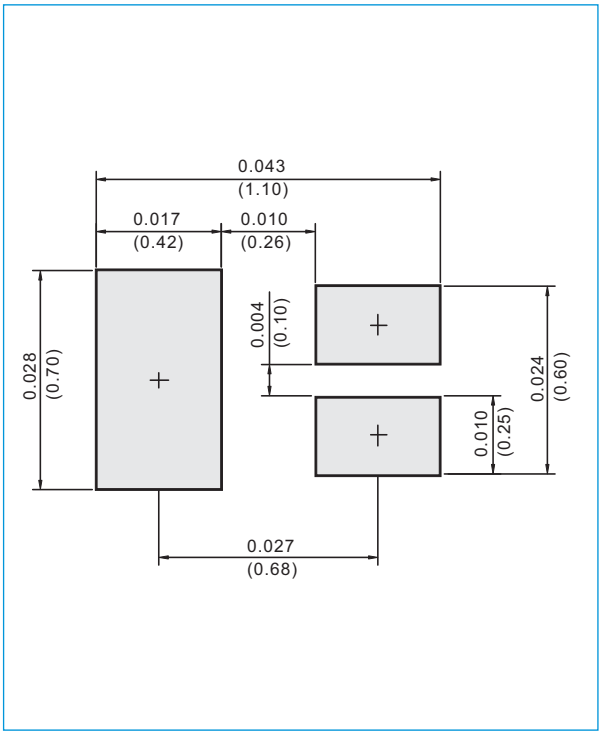
MOUNTING PAD LAYOUT

DFN 3L | Unit: inch (mm)



ORDER INFORMATION

- Packing information

  T/R - 8K per 7" plastic Reel

LEGAL STATEMENT